



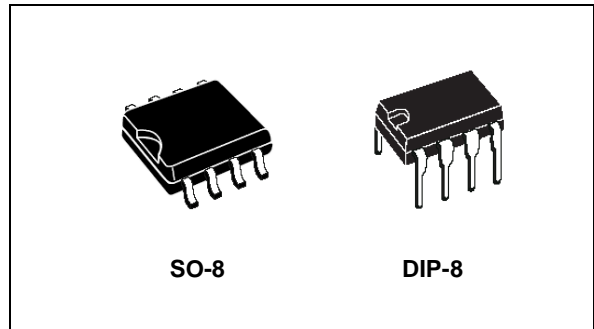
# VIPer12ADIP - E

# VIPer12AS - E

## Low Power OFF-Line SMPS Primary Switcher

### Features

- Fixed 60kHz Switching Frequency
- 9V to 38V Wide Range  $V_{DD}$  Voltage
- Current Mode Control
- Auxiliary Undervoltage Lockout with Hysteresis
- High Voltage Start-up Current Source
- Overtemperature, Overcurrent and Overvoltage Protection with Auto-Restart
- Typical power capability
  - European (195 - 265 Vac) 8W for SO-8, 13W for DIP-8
  - European (85 - 265 Vac) 5W for SO-8, 8W for DIP-8



Typical applications cover off line power supplies for battery charger adapters, standby power supplies for TV or monitors, auxiliary supplies for motor control, etc.

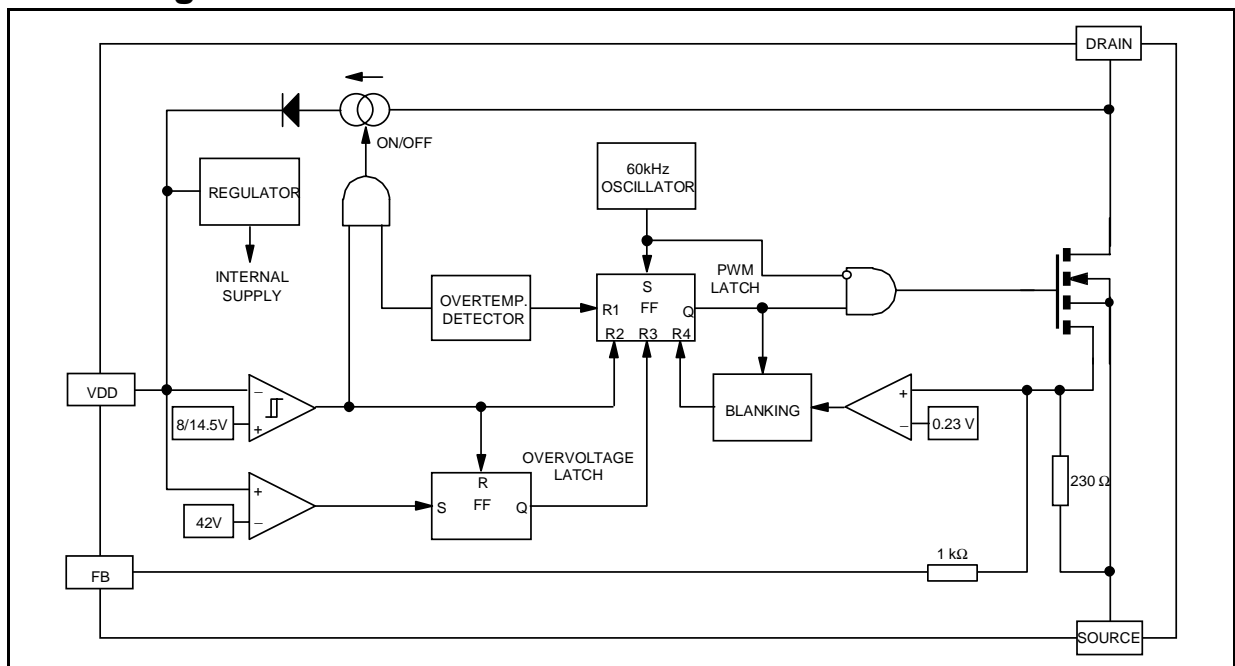
The internal control circuit offers the following benefits:

- Large input voltage range on the  $V_{DD}$  pin accommodates changes in auxiliary supply voltage. This feature is well adapted to battery charger adapter configurations.
- Automatic burst mode in low load condition.
- Overvoltage protection in HICCUP mode.

### Description

The VIPer12A combines a dedicated current mode PWM controller with a high voltage Power MOSFET on the same silicon chip.

### Block diagram



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# 1 Electrical data

## 1.1 Maximum rating

Stressing the device above the rating listed in the “Absolute Maximum Ratings” table may cause permanent damage to the device. These are stress ratings only and operation of the device at these or any other conditions above those indicated in the Operating sections of this specification is not implied. Exposure to Absolute Maximum Rating conditions for extended periods may affect device reliability. Refer also to the STMicroelectronics SURE Program and other relevant quality documents.

**Table 1. Absolute maximum rating**

Symbol	Parameter	Value	Unit
$V_{DS(sw)}$	Switching drain source voltage ( $T_J = 25 \dots 125^\circ\text{C}$ ) <i>Note 1</i>	-0.3 ... 730	V
$V_{DS(st)}$	Start-up drain source voltage ( $T_J = 25 \dots 125^\circ\text{C}$ ) <i>Note 2</i>	-0.3 ... 400	V
$I_D$	Continuous drain current	Internally limited	A
$V_{DD}$	Supply voltage	0 ... 50	V
$I_{FB}$	Feedback current	3	mA
$V_{ESD}$	Electrostatic discharge: Machine model ( $R = 0\Omega$ ; $C = 200\text{pF}$ )	200	V
	Charged device model	1.5	kV
$T_J$	Junction operating temperature	Internally limited	$^\circ\text{C}$
$T_C$	Case operating temperature	-40 to 150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature	-55 to 150	$^\circ\text{C}$

- Note: 1 This parameter applies when the start-up current source is OFF. This is the case when the  $V_{DD}$  voltage has reached  $V_{DDon}$  and remains above  $V_{DDoff}$ .
- 2 This parameter applies when the start up current source is on. This is the case when the  $V_{DD}$  voltage has not yet reached  $V_{DDon}$  or has fallen below  $V_{DDoff}$ .

## 1.2 Thermal data

**Table 2. Thermal data**

Symbol	Parameter		SO-8	DIP-8	Unit
$R_{thJC}$	Thermal Resistance Junction-case	Max	25	15	$^\circ\text{C}/\text{W}$
$R_{thJA}$	Thermal Resistance Ambient-case <sup>(1)</sup>	Max	55	45	$^\circ\text{C}/\text{W}$

1. When mounted on a standard single-sided FR4 board with 200 mm<sup>2</sup> of Cu (at least 35  $\mu\text{m}$  thick) connected to all DRAIN pins.

## 2 Electrical characteristics

$T_J = 25^\circ\text{C}$ ,  $V_{DD} = 18\text{V}$ , unless otherwise specified

**Table 3. Power section**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$BV_{DSS}$	Drain-source voltage	$I_D = 1\text{mA}$ ; $V_{FB} = 2\text{V}$	730			V
$I_{DSS}$	OFF State drain current	$V_{DS} = 500\text{V}$ ; $V_{FB} = 2\text{V}$ ; $T_J = 125^\circ\text{C}$			0.1	mA
$r_{DS(on)}$	Static drain-source ON state resistance	$I_D = 0.2\text{A}$ $I_D = 0.2\text{A}$ ; $T_J = 100^\circ\text{C}$		27	30 54	$\Omega$
$t_f$	Fall time	$I_D = 0.1\text{A}$ ; $V_{IN} = 300\text{V}$ <i>Note 1</i> (See <a href="#">Figure 8 on page 13</a> )		100		ns
$t_r$	Rise time	$I_D = 0.2\text{A}$ ; $V_{IN} = 300\text{V}$ <i>Note 1</i> (See <a href="#">Figure 8 on page 13</a> )		50		ns
$C_{OSS}$	Drain capacitance	$V_{DS} = 25\text{V}$		40		pF

Note: 1 On clamped inductive load

**Table 4. Supply section**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{DDch}$	Start-up charging current	$V_{DS} = 100\text{V}$ ; $V_{DD} = 5\text{V} \dots V_{DDon}$ (See <a href="#">Figure 9 on page 13</a> )		-1		mA
$I_{DDoff}$	Start-up charging current in thermal shutdown	$V_{DD} = 5\text{V}$ ; $V_{DS} = 100\text{V}$ $T_J > T_{SD} - T_{HYST}$	0			mA
$I_{DD0}$	Operating supply current not switching	$I_{FB} = 2\text{mA}$		3	5	mA
$I_{DD1}$	Operating supply current switching	$I_{FB} = 0.5\text{mA}$ ; $I_D = 50\text{mA}$ <i>Note 2</i>		4.5		mA
$D_{RST}$	Restart duty-cycle	(See <a href="#">Figure 10 on page 13</a> )		16		%
$V_{DDoff}$	$V_{DD}$ Undervoltage shutdown threshold	(See <a href="#">Figure 9</a> , <a href="#">Figure 10 on page 13</a> )	7	8	9	V
$V_{DDon}$	$V_{DD}$ Start-up threshold	(See <a href="#">Figure 9</a> , <a href="#">Figure 10 on page 13</a> )	13	14.5	16	V
$V_{DDhyst}$	$V_{DD}$ Threshold hysteresis	(See <a href="#">Figure 9 on page 13</a> )	5.8	6.5	7.2	V
$V_{DDovp}$	$V_{DD}$ Overvoltage threshold		38	42	46	V

2 These test conditions obtained with a resistive load are leading to the maximum conduction time of the device.

**Table 5. Oscillation section**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$F_{OSC}$	Oscillator frequency total variation	$V_{DD} = V_{DDoff} \dots 35V$ ; $T_J = 0 \dots 100^\circ C$	54	60	66	kHz

**Table 6. PWM Comparator section**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$G_{ID}$	$I_{FB}$ to $I_D$ current gain	(See <a href="#">Figure 11 on page 14</a> )		320		
$I_{Dim}$	Peak current limitation	$V_{FB} = 0V$ (See <a href="#">Figure 11 on page 14</a> )	0.32	0.4	0.48	A
$I_{FBsd}$	$I_{FB}$ Shutdown current	(See <a href="#">Figure 11 on page 14</a> )		0.9		mA
$R_{FB}$	FB Pin input impedance	$I_D = 0mA$ (See <a href="#">Figure 11 on page 14</a> )		1.2		k $\Omega$
$t_d$	Current sense delay to turn-OFF	$I_D = 0.2A$		200		ns
$t_b$	Blanking time			500		ns
$t_{ONmin}$	Minimum Turn-ON time			700		ns

**Table 7. Overtemperature section**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$T_{SD}$	Thermal shutdown temperature	(See <a href="#">Figure 12 on page 14</a> )	140	170		$^\circ C$
$T_{HYST}$	Thermal shutdown hysteresis	(See <a href="#">Figure 12 on page 14</a> )		40		$^\circ C$

**Table 8. Typical Power Capability**

Mains type	SO-8	DIP-8
European (195 - 265 Vac)	8W	13W
US / Wide range (85 - 265 Vac)	5W	8W

### 3 Pin connections and function

Figure 1. Pin connection

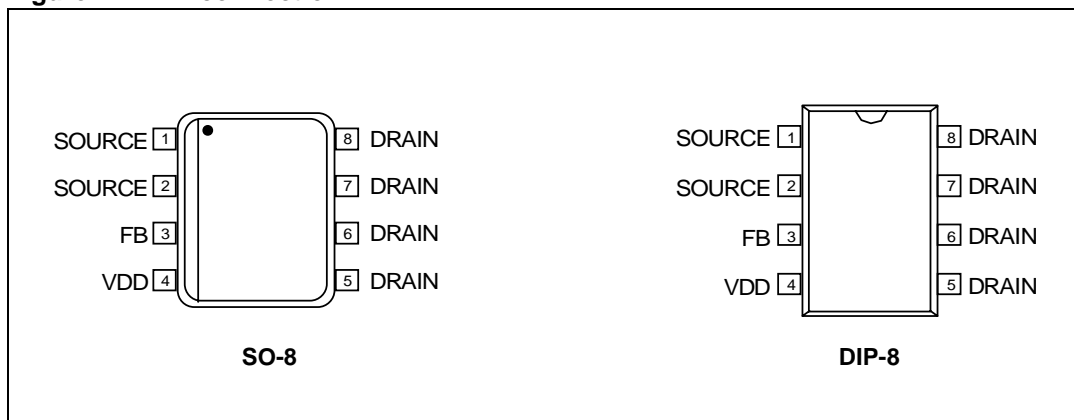


Figure 2. Current and voltage conventions

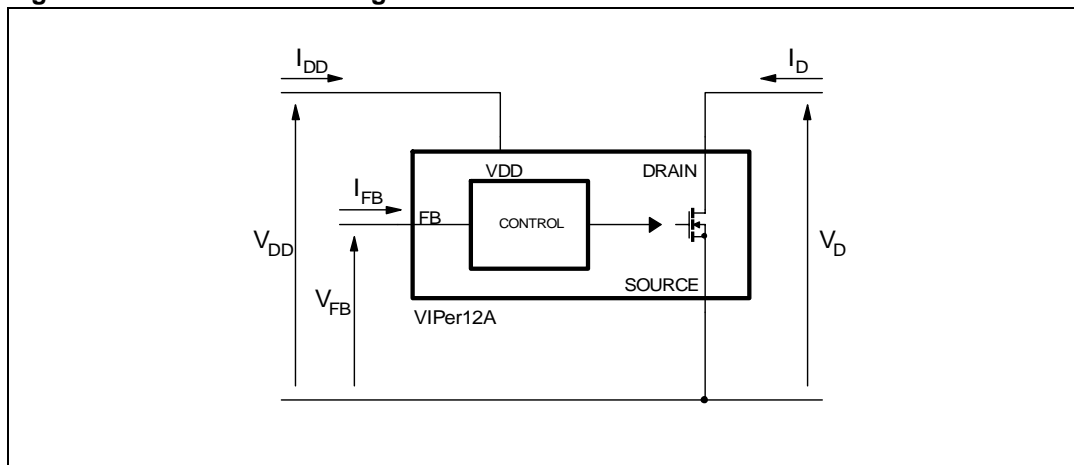


Table 9. Pin function

Pin Name	Pin Function
V <sub>DD</sub>	Power supply of the control circuits. Also provides a charging current during start up thanks to a high voltage current source connected to the drain. For this purpose, an hysteresis comparator monitors the V <sub>DD</sub> voltage and provides two thresholds: - V <sub>DDon</sub> : Voltage value (typically 14.5V) at which the device starts switching and turns off the start up current source. - V <sub>DDoff</sub> : Voltage value (typically 8V) at which the device stops switching and turns on the start up current source.
SOURCE	Power MOSFET source and circuit ground reference.
DRAIN	Power MOSFET drain. Also used by the internal high voltage current source during start up phase for charging the external V <sub>DD</sub> capacitor.
FB	Feedback input. The useful voltage range extends from 0V to 1V, and defines the peak drain MOSFET current. The current limitation, which corresponds to the maximum drain current, is obtained for a FB pin shorted to the SOURCE pin.



## 5 Wide range of $V_{DD}$ voltage

The  $V_{DD}$  pin voltage range extends from 9V to 38V. This feature offers a great flexibility in design to achieve various behaviors. In [Figure 3 on page 7](#) a forward configuration has been chosen to supply the device with two benefits:

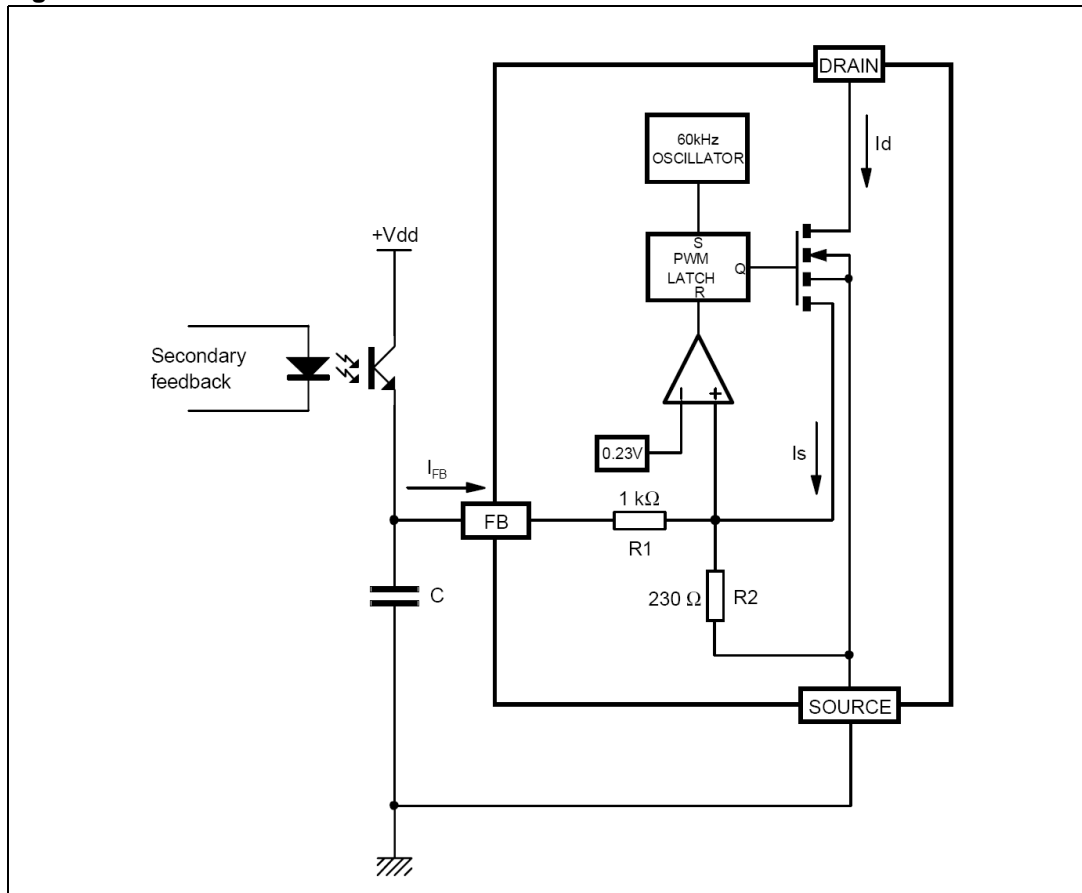
- As soon as the device starts switching, it immediately receives some energy from the auxiliary winding. C5 can be therefore reduced and a small ceramic chip (100nF) is sufficient to insure the filtering function. The total start up time from the switch on of input voltage to output voltage presence is dramatically decreased.
- The output current characteristic can be maintained even with very low or zero output voltage. Since the TSM101 is also supplied in forward mode, it keeps the current regulation up whatever the output voltage is. The  $V_{DD}$  pin voltage may vary as much as the input voltage, that is to say with a ratio of about 4 for a wide range application.



## 6 Feedback pin principle of operation

A feedback pin controls the operation of the device. Unlike conventional PWM control circuits which use a voltage input (the inverted input of an operational amplifier), the FB pin is sensitive to current. *Figure 4.* presents the internal current mode structure.

**Figure 4. Internal current control structure**



The Power MOSFET delivers a sense current  $I_s$  which is proportional to the main current  $I_d$ .  $R_2$  receives this current and the current coming from the FB pin. The voltage across  $R_2$  is then compared to a fixed reference voltage of about 0.23V. The MOSFET is switched off when the following equation is reached:

$$R_2 \cdot (I_s + I_{FB}) = 0.23V$$

By extracting  $I_s$ :

$$I_s = \frac{0.23V}{R_2} - I_{FB}$$

Using the current sense ratio of the MOSFET  $G_{ID}$ :

$$I_D = G_{ID} \cdot I_s = G_{ID} \cdot \left( \frac{0.23V}{R_2} - I_{FB} \right)$$

The current limitation is obtained with the FB pin shorted to ground ( $V_{FB} = 0V$ ). This leads to a negative current sourced by this pin, and expressed by:

$$I_{FB} = -\frac{0.23V}{R_1}$$

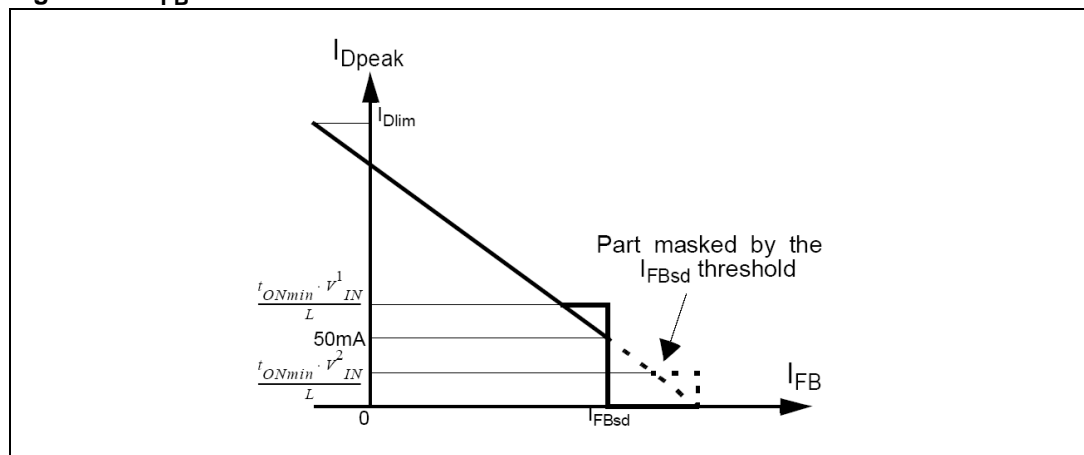
By reporting this expression in the previous one, it is possible to obtain the drain current limitation  $I_{Dlim}$ :

$$I_{Dlim} = G_{ID} \cdot 0.23V \cdot \left(\frac{1}{R_2} + \frac{1}{R_1}\right)$$

In a real application, the FB pin is driven with an optocoupler as shown on [Figure 4](#), which acts as a pull up. So, it is not possible to really short this pin to ground and the above drain current value is not achievable. Nevertheless, the capacitor C is averaging the voltage on the FB pin, and when the optocoupler is off (start up or short circuit), it can be assumed that the corresponding voltage is very close to 0V.

For low drain currents, the formula (1) is valid as long as  $I_{FB}$  satisfies  $I_{FB} < I_{FBsd}$ , where  $I_{FBsd}$  is an internal threshold of the VIPer12A. If  $I_{FB}$  exceeds this threshold the device will stop switching. This is represented on [Figure 11 on page 14](#), and  $I_{FBsd}$  value is specified in the PWM COMPARATOR SECTION. Actually, as soon as the drain current is about 12% of  $I_{Dlim}$ , that is to say 50 mA, the device will enter a burst mode operation by missing switching cycles. This is especially important when the converter is lightly loaded.

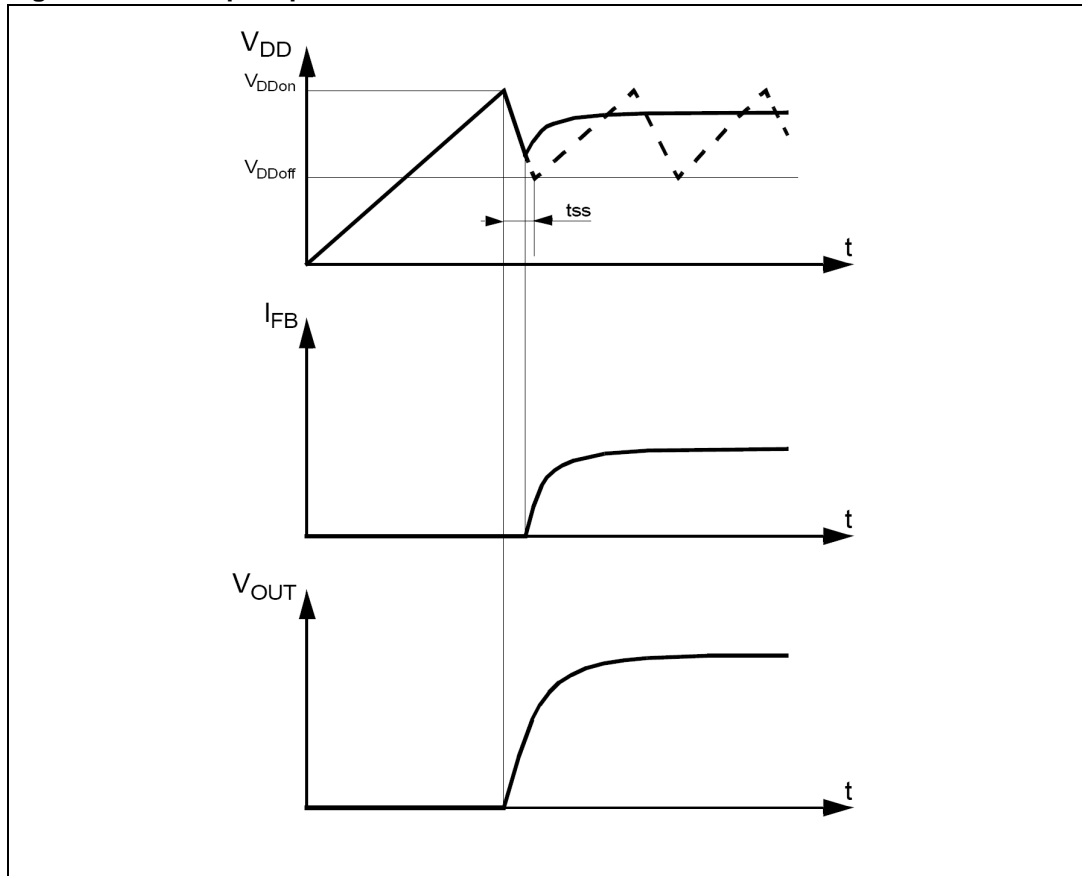
**Figure 5.  $I_{FB}$  Transfer function**



It is then possible to build the total DC transfer function between  $I_D$  and  $I_{FB}$  as shown on [Figure 5 on page 10](#). This figure also takes into account the internal blanking time and its associated minimum turn on time. This imposes a minimum drain current under which the device is no more able to control it in a linear way. This drain current depends on the primary inductance value of the transformer and the input voltage. Two cases may occur, depending on the value of this current versus the fixed 50mA value, as described above.

## 7 Startup sequence

Figure 6. Startup sequence



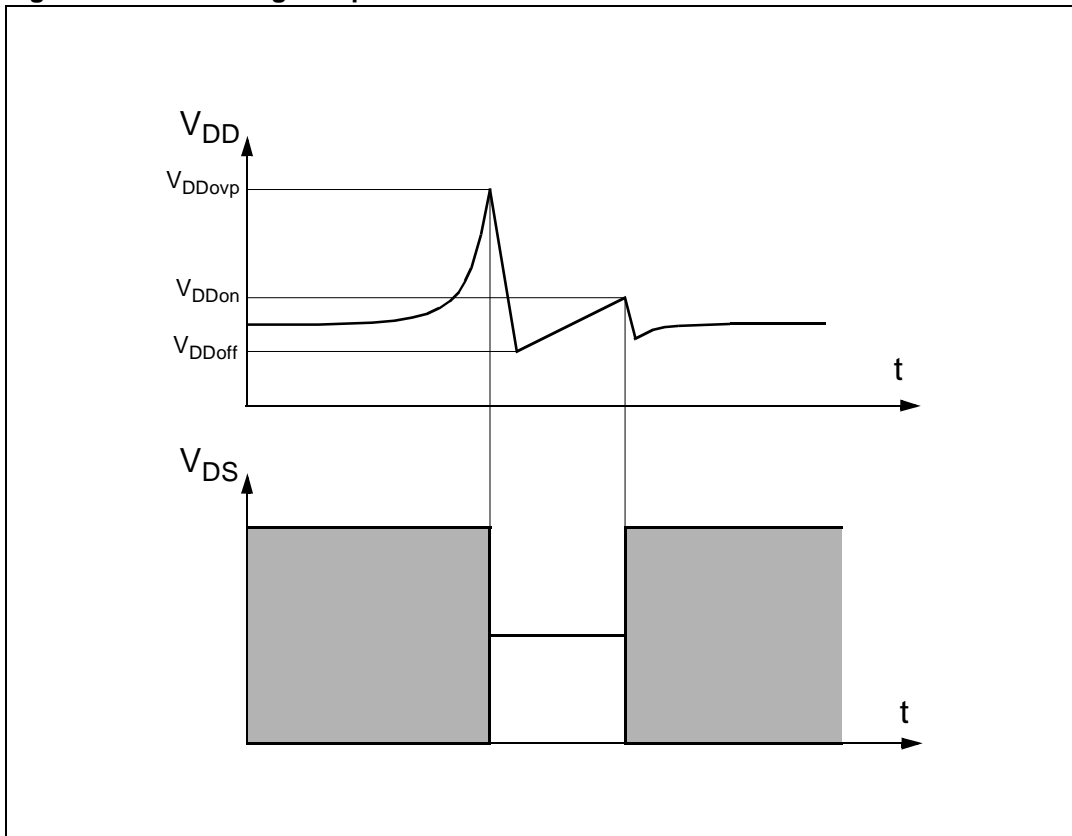
This device includes a high voltage start up current source connected on the drain of the device. As soon as a voltage is applied on the input of the converter, this start up current source is activated as long as  $V_{DD}$  is lower than  $V_{DD(on)}$ . When reaching  $V_{DD(on)}$ , the start up current source is switched off and the device begins to operate by turning on and off its main power MOSFET. As the FB pin does not receive any current from the optocoupler, the device operates at full current capacity and the output voltage rises until reaching the regulation point where the secondary loop begins to send a current in the optocoupler. At this point, the converter enters a regulated operation where the FB pin receives the amount of current needed to deliver the right power on secondary side.

This sequence is shown in [Figure 6](#). Note that during the real starting phase  $t_{ss}$ , the device consumes some energy from the  $V_{DD}$  capacitor, waiting for the auxiliary winding to provide a continuous supply. If the value of this capacitor is too low, the start up phase is terminated before receiving any energy from the auxiliary winding and the converter never starts up. This is illustrated also in the same figure in dashed lines.

## 8 Overvoltage threshold

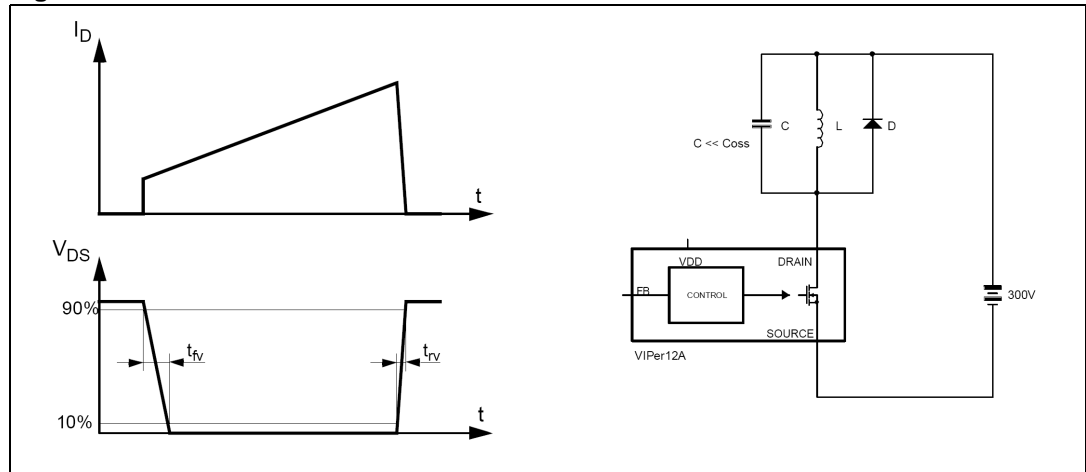
An overvoltage detector on the  $V_{DD}$  pin allows the VIPer12A to reset itself when  $V_{DD}$  exceeds  $V_{DDovp}$ . This is illustrated in [Figure 7.](#), which shows the whole sequence of an overvoltage event. Note that this event is only latched for the time needed by  $V_{DD}$  to reach  $V_{DDoff}$ , and then the device resumes normal operation automatically.

**Figure 7. Overvoltage Sequence**

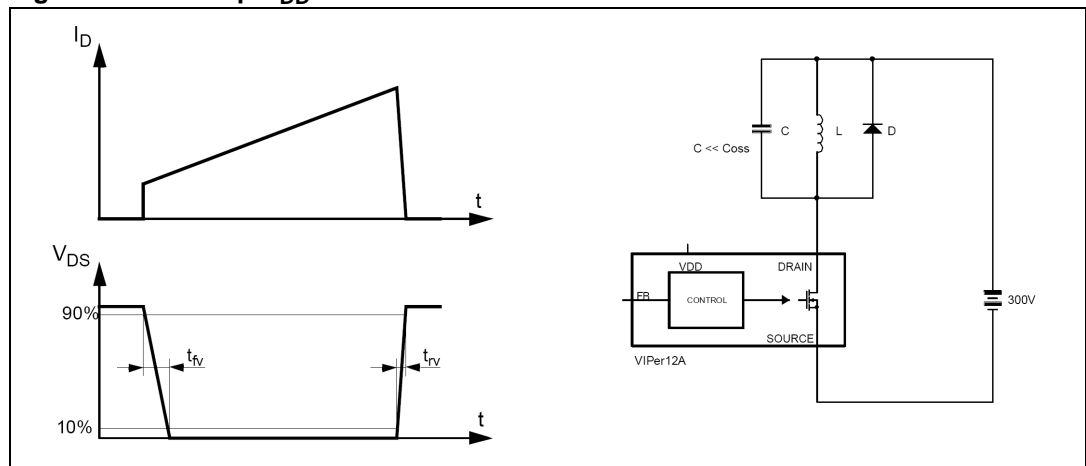


# 9 Operation pictures

**Figure 8. Rise and Fall time**



**Figure 9. Start-up V<sub>DD</sub> current**



**Figure 10. Restart duty-cycle**

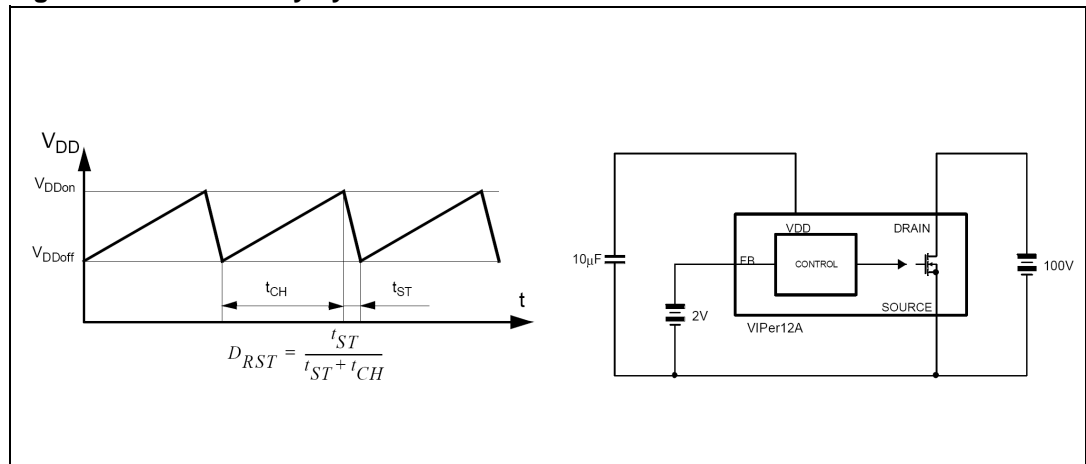


Figure 11. Peak drain current Vs. feedback current

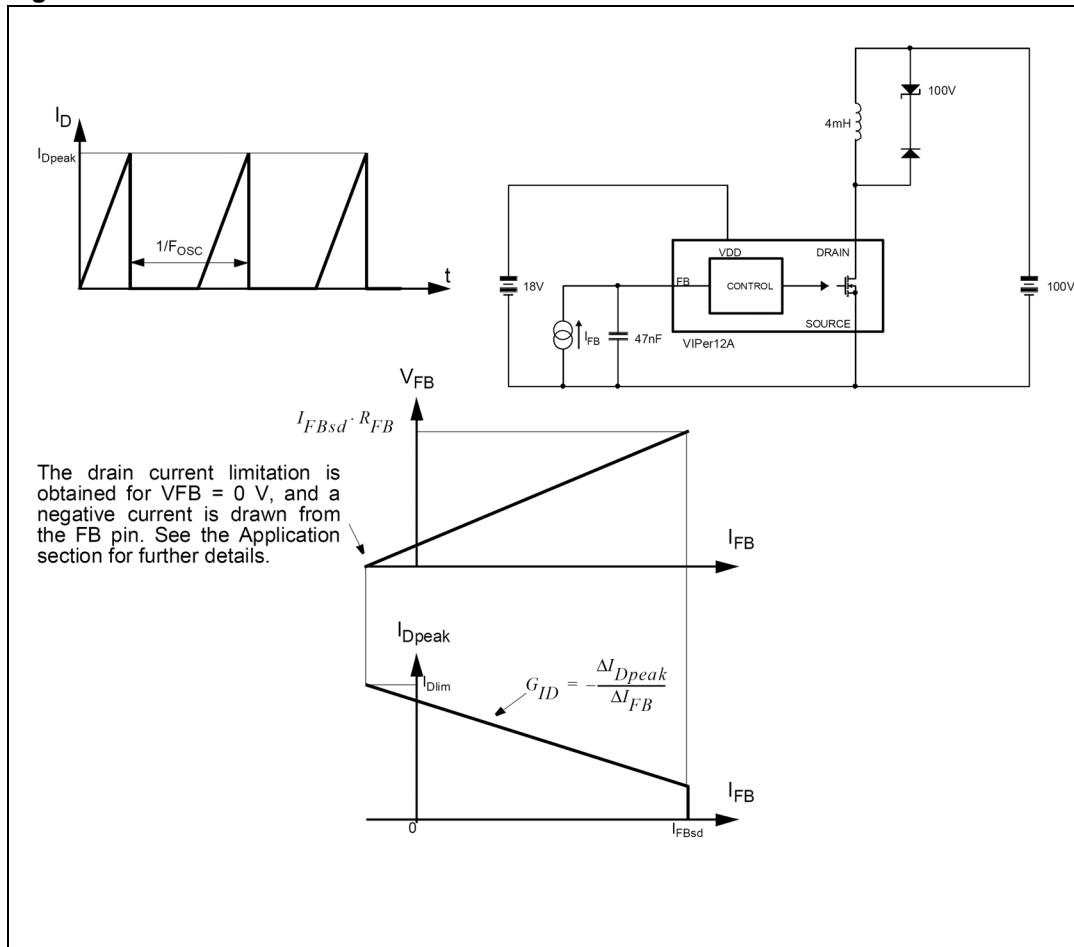


Figure 12. Thermal shutdown

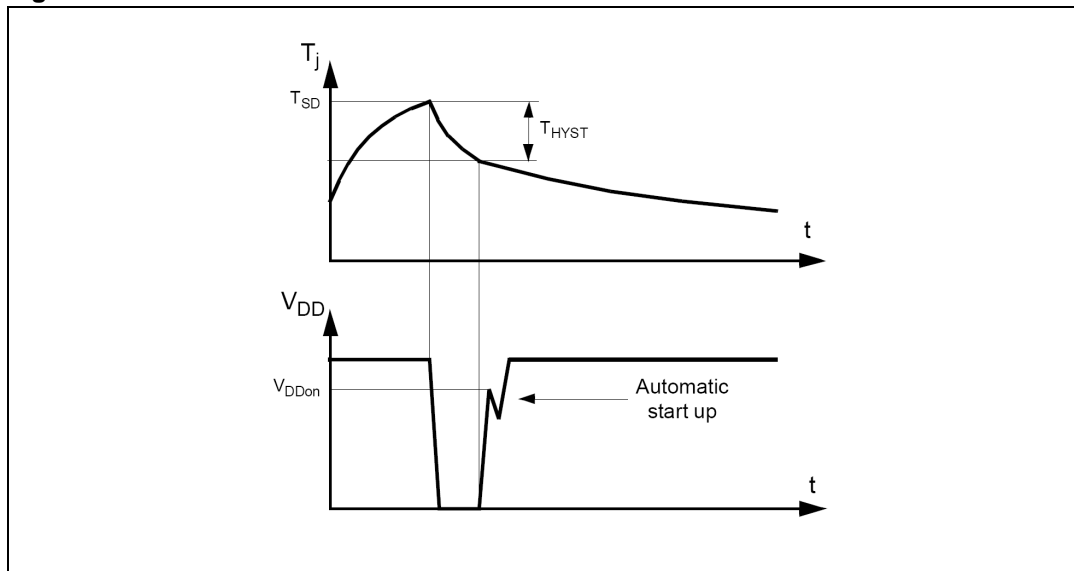


Figure 13. Switching frequency Vs. temperature

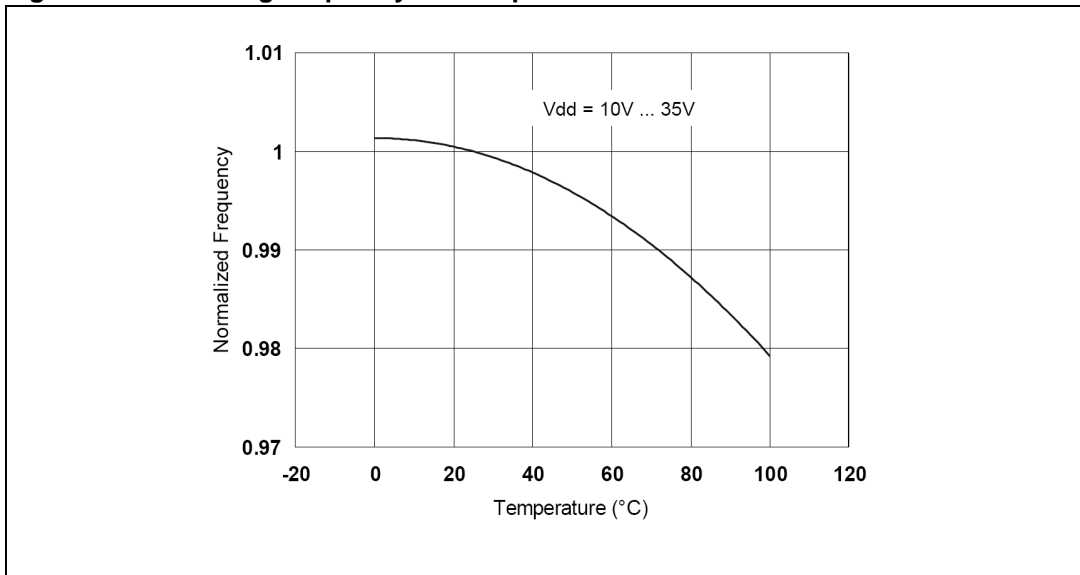
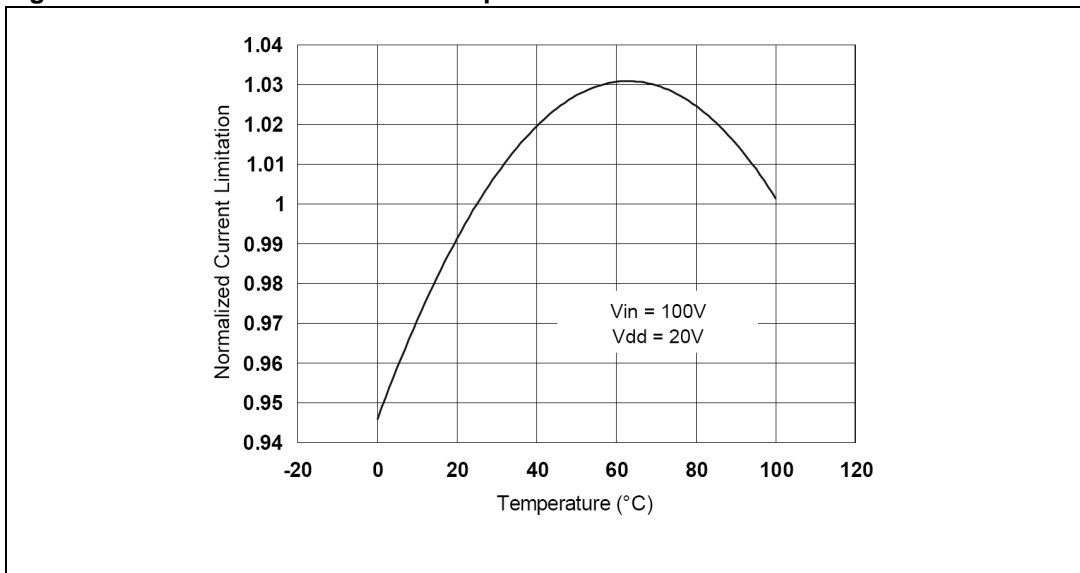


Figure 14. Current Limitation vs. Temperature



## 10 Mechanical Data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second Level Interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: [www.st.com](http://www.st.com).



Table 10. DIP8 Mechanical Data

Dimensions			
Ref.	Databook (mm)		
	Nom.	Min	Max
A			5.33
A1	0.38		
A2	2.92	3.30	4.95
b	0.36	0.46	0.56
b2	1.14	1.52	1.78
c	0.20	0.25	0.36
D	9.02	9.27	10.16
E	7.62	7.87	8.26
E1	6.10	6.35	7.11
e		2.54	
eA		7.62	
eB			10.92
L	2.92	3.30	3.81
Package Weight	Gr. 470		

Figure 15. Package Dimensions

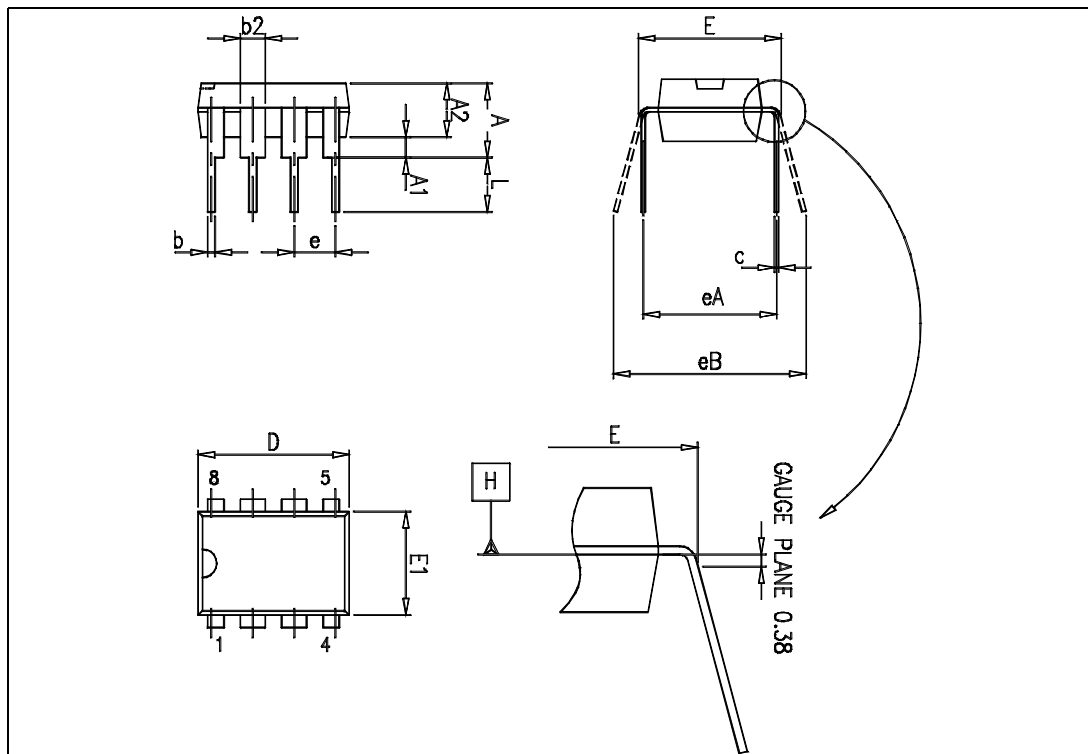
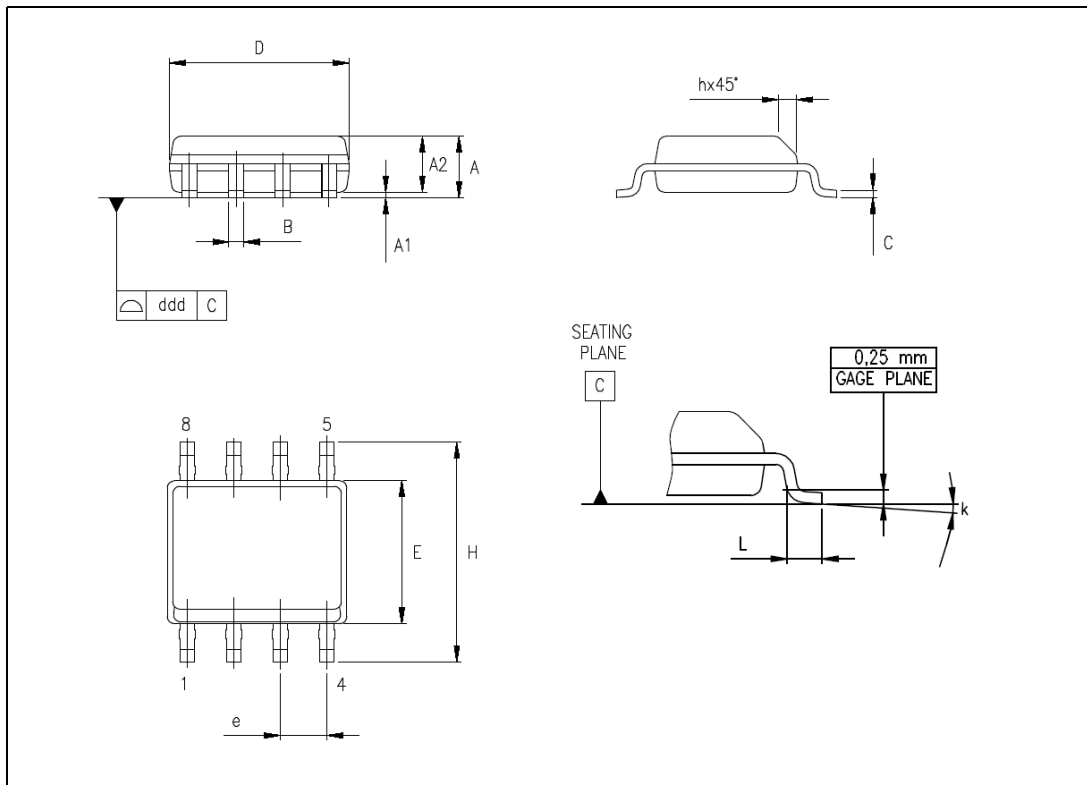


Table 11. SO8 Mechanical Data

Dimensions			
Ref.	Databook (mm)		
	Nom.	Min	Max
A	1.35		1.75
A1	0.10		0.25
A2	1.10		1.65
B	0.33		0.51
C	0.19		0.25
D	4.80		5.00
E	3.80		4.00
e		1.27	
H	5.80		6.20
h	0.25		0.50
L	0.40		1.27
k	8° (max.)		
ddd			0.1

Figure 16. Package Dimensions



## 11 Order codes

**Table 12. Order codes**

<b>Part Number</b>	<b>Package</b>	<b>Shipment</b>
VIPER12ASTR-E	SO-8	Tape and Reel
VIPer12AS - E	SO-8	Tube
VIPer12ADIP - E	DIP-8	Tube

## 12 Revision history

**Table 13. Document revision history**

Date	Revision	Changes
09-Jan-2006	1	Initial release.

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